

## Preliminary Technical Data

## AD8506

### FEATURES

- High linearity**
- PSRR: 105dB minimum**
- CMRR: 105 dB typical**
- Very low supply current: 20  $\mu$ A/amp maximum**
- 1.8 V to 5.5 V single-supply operation**
- Rail-to-rail input and output**
- Low noise 2.9  $\mu$ V p-p from 0.1 Hz to 10 Hz**
- 4 mV offset voltage maximum**
- Very low input bias current: 1 pA typical**

### APPLICATIONS

- Pressure and position sensors**
- Remote security**
- Medical monitors**
- Battery-powered consumer equipment**
- Hazard detectors**

### GENERAL DESCRIPTION

The AD8506 is a dual micro-power amplifier featuring rail-to-rail input and output swings while operating from a 1.8 V to 5.5 V single power supply.

Employing a new circuit technology, these low cost amplifiers offer high linearity (excellent PSRR and CMRR performance) and very low bias current, while operating with a supply current of less than 20  $\mu$ A per amplifier.

This combination of features makes the AD8506 amplifier an ideal choice for battery-powered applications since it minimizes errors due to power supply voltage variations over the battery's lifetime and maintains relatively high CMRR for a rail-to-rail op amp.

Remote battery-powered sensors, handheld instrumentation and consumer equipment, hazard detection (for example, smoke, fire, and gas), and patient monitors can benefit from the features of the AD8506 amplifier.

The AD8506 is specified for both the industrial temperature range ( $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ ) and the extended industrial temperature range ( $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ ). AD8506 dual amplifiers are available in the standard 8-lead MSOP and WLCSP.

### PIN CONFIGURATIONS

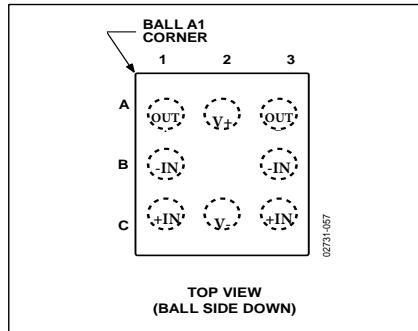


Figure 1. 8-Ball WLCSP

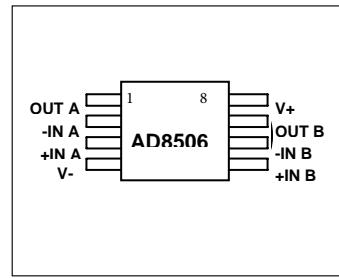


Figure 2. 8-Lead MSOP (RM Suffix)

Rev. PrA

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## REVISION HISTORY

10/07—Revision 0: Initial Version

## SPECIFICATIONS

### ELECTRICAL CHARACTERISTICS – $V_S = 5V$

$V_S = 5V$ ,  $V_{CM} = V_S/2$ ,  $T_A = 25^\circ C$ , unless otherwise specified.

Table 1.

| Parameter                    | Symbol                   | Conditions                             | Min  | Typ  | Max      | Unit                  |
|------------------------------|--------------------------|--|------|------|----------|-----------------------|
| INPUT CHARACTERISTICS        |                          |  |      |      |          |                       |
| Offset Voltage               | $V_{OS}$                 | $0V < V_{CM} < 5V$                     |      | 4    |          | mV                    |
| Input Bias Current           | $I_B$                    | $-40^\circ C < T_A < +85^\circ C$      | 1    | 10   | 100      | pA                    |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     |      |      | 600      | pA                    |
| Input Offset Current         | $I_{OS}$                 | $-40^\circ C < T_A < +85^\circ C$      | 0.5  | 5    | 50       | pA                    |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     |      |      | 100      | pA                    |
| Input Voltage Range          |                          | $-40^\circ C < T_A < +125^\circ C$     | 0    | 5    |          | V                     |
| Common-Mode Rejection Ratio  | $CMRR$                   | $V_{CM} = 0V \text{ to } 5V$           | 90   | 105  |          | dB                    |
|                              |                          | $-40^\circ C < T_A < +85^\circ C$      | 90   | 105  |          | dB                    |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     | 90   |      |          | dB                    |
| Large Signal Voltage Gain    | $A_{VO}$                 | $0.05 < V_{OUT} < 4.95$                | 110  | 130  |          | dB                    |
|                              |                          | $-40^\circ C < T_A < +85^\circ C$      | 100  |      |          | dB                    |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     | 100  |      |          | dB                    |
| Offset Voltage Drift         | $\Delta V_{OS}/\Delta T$ | $-40^\circ C < T_A < +85^\circ C$      |      | 2.2  |          | $\mu V/^\circ C$      |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     |      | 2.2  |          | $\mu V/^\circ C$      |
| OUTPUT CHARACTERISTICS       |                          |  |      |      |          |                       |
| Output Voltage High          | $V_{OH}$                 | $R_L = 100 k\Omega \text{ to GND}$     | 4.95 | 4.99 |          | V                     |
|                              |                          | $R_L = 10 k\Omega \text{ to GND}$      | 4.85 | 4.9  |          | V                     |
| Output Voltage Low           | $V_{OL}$                 | $R_L = 100 k\Omega \text{ to } V_S$    | 2    | 50   | 150      | $\mu V$               |
|                              |                          | $R_L = 10 k\Omega \text{ to } V_S$     | 8    |      | $\pm 60$ | $\mu V$               |
| Short Circuit Limit          | $I_{SC}$                 | $-40^\circ C \text{ to } +85^\circ C$  |      |      | $\pm 80$ | mA                    |
|                              |                          | $-40^\circ C \text{ to } +125^\circ C$ |      |      | TBD      | mA                    |
| POWER SUPPLY                 |                          |  |      |      |          |                       |
| Power Supply Rejection Ratio | $PSRR$                   | $V_S = 1.8V \text{ to } 5V$            | 105  | 120  |          | dB                    |
|                              |                          | $-40^\circ C \text{ to } +85^\circ C$  | 100  | 120  |          | dB                    |
|                              |                          | $-40^\circ C \text{ to } +125^\circ C$ | 90   | 120  |          | dB                    |
| Supply Current/Amplifier     | $I_{SY}$                 | $V_O = V_S/2$                          |      | 18   | 20       | $\mu A$               |
|                              |                          | $-40^\circ C < T_A < +125^\circ C$     |      | 28   |          | $\mu A$               |
| DYNAMIC PERFORMANCE          |                          |  |      |      |          |                       |
| Slew Rate                    | $SR$                     |  |      | 12   |          | $mV/\mu s$            |
| Gain Bandwidth Product       | $GBP$                    |  |      | 150  |          | kHz                   |
| NOISE PERFORMANCE            |                          |  |      |      |          |                       |
| Peak-to-Peak Noise           | $e_{n,p-p}$              | $f = 0.1 \text{ to } 10 \text{ Hz}$    |      | 2.9  |          | $\mu V \text{ p-p}$   |
| Voltage Noise Density        | $e_n$                    | $f = 1 \text{ kHz}$                    |      | 48   |          | $nV/\sqrt{\text{Hz}}$ |
| Current Noise Density        | $i_n$                    | $f = 10 \text{ Hz}$                    |      | TBD  |          | $fA/\sqrt{\text{Hz}}$ |

**ELECTRICAL CHARACTERISTICS –  $V_S = 1.8V$** 

$V_S = 1.8\text{ V}$ ,  $V_{CM} = V_S/2$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Table 2.

| Parameter                     | Symbol                   | Conditions                                     | Min  | Typ     | Max     | Unit                         |
|-------------------------------|--------------------------|--|------|---------|---------|------------------------------|
| <b>INPUT CHARACTERISTICS</b>  |                          |  |      |         |         |                              |
| Offset Voltage                | $V_{OS}$                 | $0\text{ V} < V_{CM} < 1.8\text{ V}$           |      |         | 4       | $\mu\text{V}$                |
| Input Bias Current            | $I_B$                    | $-40^\circ\text{C} < T_A < +85^\circ\text{C}$  |      | 1       | 10      | $\text{pA}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ |      |         | 100     | $\text{pA}$                  |
| Input Offset Current          | $I_{OS}$                 | $-40^\circ\text{C} < T_A < +85^\circ\text{C}$  |      |         | 600     | $\text{pA}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ |      | 0.5     | 5       | $\text{pA}$                  |
| Input Voltage Range           |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ | 0    |         | 50      | $\mu\text{V}$                |
| Common-Mode Rejection Ratio   | CMRR                     | $V_{CM} = 0\text{ V}$ to $1.8\text{ V}$        | 90   | 105     |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +85^\circ\text{C}$  | 85   | 100     |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ | 85   |         |         | $\text{dB}$                  |
| Large Signal Voltage Gain     | $A_{VO}$                 | $0.05 < V_{OUT} < 1.75$                        | 110  | 130     |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +85^\circ\text{C}$  | 100  |         |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ | 100  |         |         | $\text{dB}$                  |
| Offset Voltage Drift          | $\Delta V_{OS}/\Delta T$ | $-40^\circ\text{C} < T_A < +85^\circ\text{C}$  |      | 2.2     |         | $\mu\text{V}/^\circ\text{C}$ |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ |      | 2.2     |         | $\mu\text{V}/^\circ\text{C}$ |
| <b>OUTPUT CHARACTERISTICS</b> |                          |  |      |         |         |                              |
| Output Voltage High           | $V_{OH}$                 | $R_L = 100\text{ k}\Omega$ to GND              | 1.75 | TBD     |         | $\text{V}$                   |
|                               |                          | $R_L = 10\text{ k}\Omega$ to GND               | 1.65 | 1.7     |         | $\text{V}$                   |
| Output Voltage Low            | $V_{OL}$                 | $R_L = 100\text{ k}\Omega$ to $V_S$            |      | TBD     | 50      | $\mu\text{V}$                |
|                               |                          | $R_L = 10\text{ k}\Omega$ to $V_S$             |      | TBD     | 150     | $\mu\text{V}$                |
| Short Circuit Limit           | $I_{SC}$                 | $-40^\circ\text{C}$ to $+85^\circ\text{C}$     |      | $\pm 4$ | $\pm 6$ | $\text{mA}$                  |
|                               |                          | $-40^\circ\text{C}$ to $+125^\circ\text{C}$    |      |         | TBD     | $\text{mA}$                  |
| <b>POWER SUPPLY</b>           |                          |  |      |         |         |                              |
| Power Supply Rejection Ratio  | PSRR                     | $V_S = 1.8\text{ V}$ to $5\text{ V}$           | 105  | 120     |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C}$ to $+85^\circ\text{C}$     | 100  | 120     |         | $\text{dB}$                  |
|                               |                          | $-40^\circ\text{C}$ to $+125^\circ\text{C}$    | 90   | 120     |         |                              |
| Supply Current/Amplifier      | $I_{SY}$                 | $V_O = V_S/2$                                  |      | 18      | 20      | $\mu\text{A}$                |
|                               |                          | $-40^\circ\text{C} < T_A < +125^\circ\text{C}$ |      | 28      |         | $\mu\text{A}$                |
| <b>DYNAMIC PERFORMANCE</b>    |                          |  |      |         |         |                              |
| Slew Rate                     | SR                       |  |      | 12      |         | $\text{mV}/\mu\text{s}$      |
| Gain Bandwidth Product        | GBP                      |  |      | 150     |         | $\text{kHz}$                 |
| <b>NOISE PERFORMANCE</b>      |                          |  |      |         |         |                              |
| Peak-to-Peak Noise            | $e_{n,p-p}$              | $f = 0.1$ to $10\text{ Hz}$                    |      | 2.9     |         | $\mu\text{V p-p}$            |
| Voltage Noise Density         | $e_n$                    | $f = 1\text{ kHz}$                             |      | 48      |         | $\text{nV}/\sqrt{\text{Hz}}$ |
| Current Noise Density         | $i_n$                    | $f = 10\text{ Hz}$                             |      | TBD     |         | $\text{fA}/\sqrt{\text{Hz}}$ |

## ABSOLUTE MAXIMUM RATINGS

Table 3.

| Parameter                                     | Rating          |
|---|-----------------|
| Supply Voltage                                | 6 V             |
| Input Voltage                                 | $\pm V_s$       |
| Differential Input Voltage <sup>1</sup>       | $\pm V_s$       |
| Output Short-Circuit Duration to Gnd          | Indefinite      |
| Storage Temperature Range RM,<br>CB Packages  | -65°C to +150°C |
| Operating Temperature Range                   | -40°C to +125°C |
| Junction Temperature Range<br>RM, CB Packages | -65°C to +150°C |
| Lead Temperature (Soldering, 60 sec)          | 300°C           |

<sup>1</sup> Differential input voltage is limited to 5 V or the supply voltage, whichever is less.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages.

Table 4. Thermal Resistance

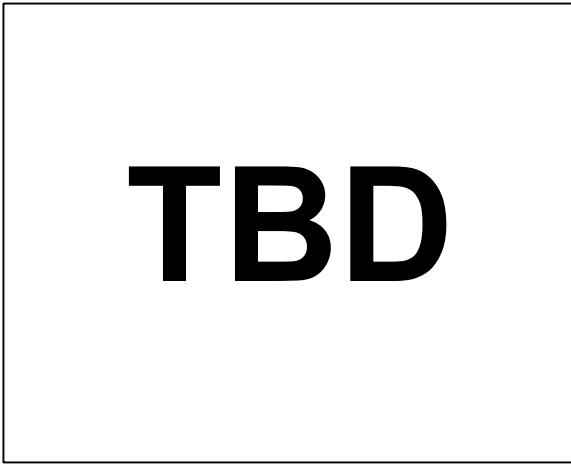
| Package Type     | $\theta_{JA}$ | $\theta_{JC}$ | Unit |
|------------------|---------------|---------------|------|
| 8-Lead MSOP (RM) | 190           | 44            | °C/W |
| 8-Ball WLCSP     | TBD           | TBD           | °C/W |

## ESD CAUTION



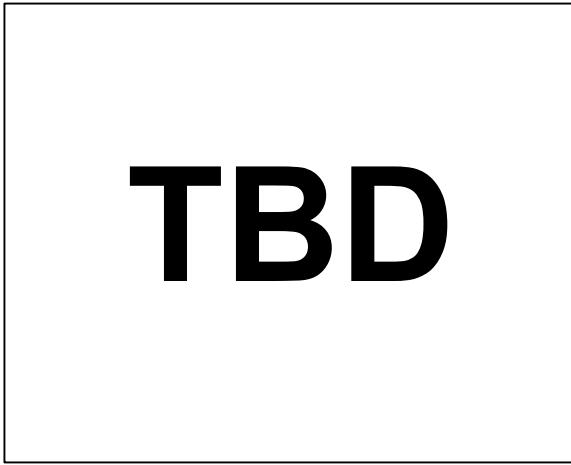
**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

## TYPICAL PERFORMANCE CHARACTERISTICS



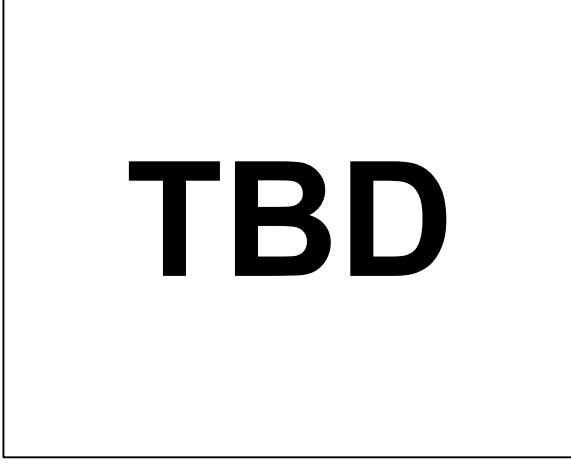
**TBD**

Figure 3



**TBD**

Figure 6



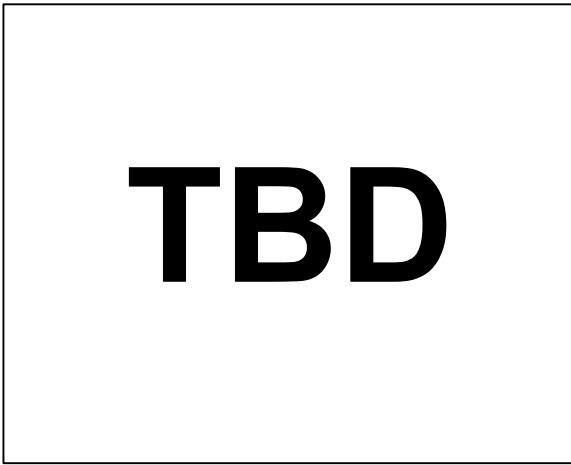
**TBD**

Figure 4



**TBD**

Figure 7



**TBD**

Figure 5

## TERMINOLOGY

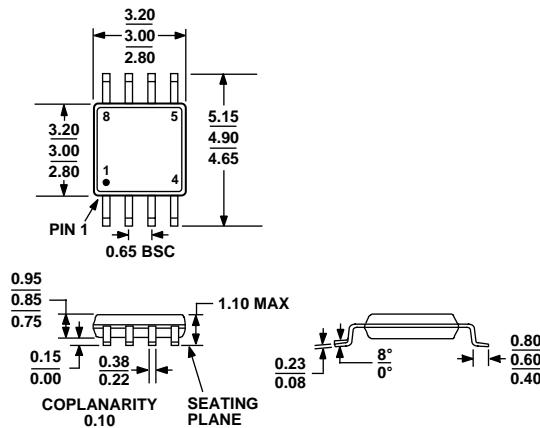
**Definition Term**

Definition

## **THEORY OF OPERATION**

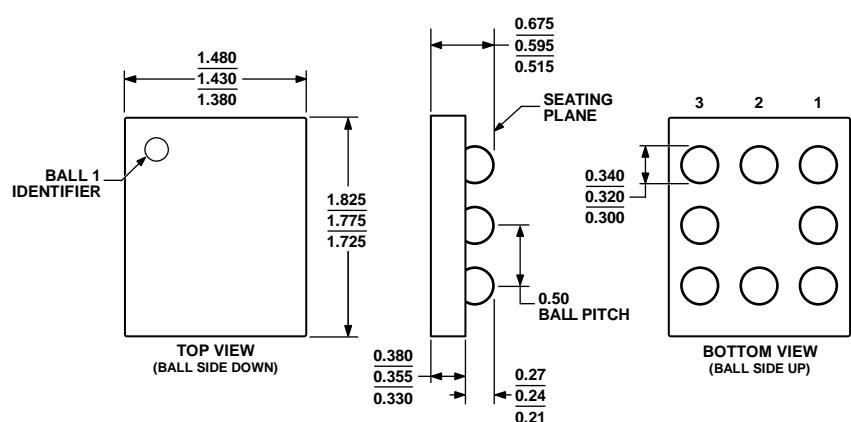
## **APPLICATIONS INFORMATION**

## OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 8. 8-Lead Mini Small Outline Package [MSOP]  
(RM-8)  
Dimensions shown in millimeters



090706-B

Figure 9. 8-Ball Wafer Level Chip Scale Package [WLCSP]  
(CB-8-1)  
Dimensions shown in millimeters

## ORDERING GUIDE

| Model                   | Temperature Range | Package Description                           | Package Option |
|-------------------------|-------------------|---|----------------|
| AD8506ARMZ <sup>1</sup> | -40°C to +125°C   | 8-Lead Mini Small Outline Package [MSOP]      | RM-8           |
| AD8506ACBZ <sup>1</sup> | -40°C to +125°C   | 8-Ball Wafer Level Chip Scale Package [WLCSP] | CB-8-1         |

<sup>1</sup> Z = RoHS Compliant Part.